

GLT6200L08/M08/N08

ADVANCED

256K x 8 Super Low Power & Low Voltage SRAM

FEATURES

- ◆ Organization: 256K x 8
- ◆ Low Data Retention Voltage: 1.5 V (min)
- ◆ Power Supply Voltage
 - GLT6200L08: 2.7 V ~ 3.6 V
 - GLT6200M08: 2.3 V ~ 2.7 V
 - GLT6200N08: 1.8 V ~ 2.3 V
- ◆ Maximum 2 μ A Standby Current
- ◆ Three-state output status and TTL compatible
- ◆ Package type; JEDEC standard 32-Pin SOP, 32-Pin TSOP I, 32-Pin Shrink TSOP I

Product Family

Organization	Part Number	V _{CC}	I _{sb1}	Speed	Temperature
256Kx8	GLT6200L/LI	2.7 ~ 3.6 V	2 μ a	70/85/100	Commercial: 0 to +70°C Industrial: -40 to +85°C
256Kx8	GLT6200M/MI	2.3 ~ 2.7 V	2 μ a	100/120/150	
256Kx8	GLT6200N/NI	1.8 ~ 2.3 V	2 μ a	150/300	

GENERAL DESCRIPTION

The GLT 6200L08/M08/N08 Super Low-Power SRAM family can support various voltage and operating temperature ranges and has various package types for user

flexibility of system design. The family also support low data retention voltage for battery back-up operations with low data retention current.

GLT6200L08/M08/N08

FUNCTIONAL BLOCK DIAGRAM

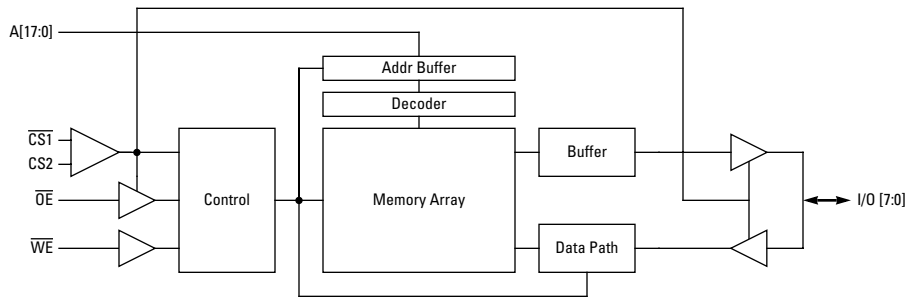


Figure 1. GLT6200L08/M08/N08 256K x 8

Signal Descriptions

Symbol	Type	Description
A[17:0]	Input	Address Inputs
\overline{WE}	Control	Write Enable Input
$\overline{CS1}$	Control	Chip Select Input
CS2	Control	Chip Select Input
\overline{OE}	Control	Output Enable Input
I/O[7:0]	I/O	Data Input/Output
V_{CC}	Power	Power
V_{SS}	Power	Ground
NC	N/A	No Connection

Functional Truth Table ^[1]

$\overline{CS1}$	CS2	\overline{WE}	\overline{OE}	Mode	I/O [7:0]	Current Mode
H	X	X	X	Not Select	High-Z	I_{SB}^1
X	L	X	X	Not Select	High-Z	I_{SB}^1
L	H	H	H	Output Disable	High-Z	I_{CC}
L	H	H	L	Read	D_{OUT}	I_{CC}
L	H	L	X	Write	D_{IN}	I_{CC}

1. X means don't care (High or Low)

ELECTRICAL SPECIFICATIONS**Absolute Maximum Ratings** ^[1]

Parameter		Rating
Voltage on any Pin Relative to V_{SS}		-0.2 V to $V_{CC} + 0.5$ V
Voltage on V_{CC} Supply Relative to V_{SS}		-0.2 V to 4.0 V
Power Dissipation		1.0 W
Storage Temperature		-55 °C to +150 °C
Operation Temperature	Commercial	0 °C to +70 °C
	Industrial	-40 °C to +85 °C
Soldering Temperature and Time		260 °C, 5 Sec (Lead Only)

- Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Recommended DC Operating Conditions ^[1] ^[2]

Symbol	Description	Product	Min	Typ ^[3]	Max	Units
V_{CC}	Supply Voltage	GLT6200L	2.7	3.3	3.6	V
		GLT6200M	2.3	2.5	2.7	V
		GLT6200N	1.8	2.0	2.3	V
V_{SS}	Ground	All Family	0	0	0	V
V_{IH}	Input High Voltage	GLT6200L	2.2	–	$V_{CC} + 0.2$ ^[4]	V
		GLT6200M	2.0	–	$V_{CC} + 0.2$ ^[4]	V
		GLT6200N	1.6	–	$V_{CC} + 0.2$ ^[4]	V
V_{IL}	Input Low Voltage	All Family	-0.2 ^[5]	–	0.4	V

- Commercial product: $T_A = 0$ to +70 °C, unless otherwise specified.
- Industrial Product: $T_A = -40$ to +85 °C, unless specified otherwise
- $T_A = 25$ °C
- $V_{IH}(\text{max}) = V_{CC} + 1.0$ V for ≤ 20 ns pulse width
- $V_{IL}(\text{min}) = -1.0$ V for ≤ 20 ns pulse width

Capacitance ^[1] ($f = 1$ MHz, $T_A = 25$ °C)

Symbol	Description	Conditions	Min	Max	Units
C_{IN}	Input Capacitance	$V_{IN} = 0$ V	-	8	pF
C_{IO}	Input/Output Capacitance	$V_{IO} = 0$ V	-	10	pF

- Capacitance is sampled, not 100% tested

GLT6200L08/M08/N08**DC Characteristics**

Symbol	Description	Test Conditions ^[1]		Min	TYP	Max	Units
I _{LI}	Input Leakage Current	V _{IN} = V _{SS} to V _{CC}		-1	-	1	μA
I _{LO}	Output Leakage Current	CS1 = V _{IH} or CS2 = V _{IL} or WE = V _{IL} or OE = V _{IH} V _{IO} = V _{SS} to V _{CC}		-1	-	1	μA
I _{CC}	Operating Power Supply Current	CS1 = V _{IL} , CS2 = V _{IH} , V _{IN} = V _{IH} or V _{IL} , I _{IO} = 0 mA		-	-	12 ^[2]	mA
I _{CC1}	Average Operating Current	Cycle time = 1 μs, 100% duty, CS1 ≤ 0.2V, CS2 ≥ V _{CC} - 0.2V, I _{IO} = 0 mA, V _{IN} ≤ 0.2 V, or V _{IN} ≥ V _{CC} - 0.2 V		-	-	15 ^[2]	mA
I _{CC2}	Average Operating Current	CS1 = V _{IL} , CS2 = V _{IH} , I _{IO} = 0 mA Min cycle, 100% duty V _{IN} = V _{IL} or V _{IH}	V _{CC} = 3.3V @ 70 ns	-	-	40 ^[3]	mA
			V _{CC} = 2.7V @ 100 ns	-	-	25	
			V _{CC} = 2.2V @ 150 ns	-	-	15	
V _{OL}	Output Low Voltage	L _{OL}	V _{CC} = 3.0/3.3V	-	-	0.4	V
			V _{CC} = 2.5V	-	-	0.4	
			V _{CC} = 2.0V	-	-	0.4	
V _{OH}	Output High Voltage	L _{OH}	V _{CC} = 3.0/3.3V	2.4	-	-	V
			V _{CC} = 2.5V	2.0	-	-	
			V _{CC} = 2.0V	1.6	-	-	
I _{SB}	Standby Current (TTL)	CS2 ≤ V _{IL} or CS1 ≥ V _{IH} , CS2 ≥ V _{IH}		-	-	0.3	mA
I _{SB1}	Standby Current (CMOS)	GLT6200x08SL	CS1 ≥ V _{CC} - 0.2V, CS2 ≥ V _{CC} - 0.2V	-	0.05 ^[4]	2 ^[5]	μA
		GLT6200x08LL	or CS2 ≤ 0.2V	-	-	10 ^[6]	μA

1. Commercial Products

T_A = 0 to 70°C, V_{CC} = 2.7 ~ 3.6V for GLT6200L Family, V_{CC} = 2.3 (min) ~ 2.7V (max) for GLT6200M Family, V_{CC} = 1.8 (min) ~ 2.3V (max) for GLT6200N Family

Industrial Product

T_A = -40 to 85°C, V_{CC} = 2.7 ~ 3.6V for GLT6200LI Family, V_{CC} = 2.3 (min) ~ 2.7V (max) for GLT6200MI Family, V_{CC} = 1.8 (min) ~ 2.3V (max) for GLT6200NI Family

- The Value is measured at V_{CC} = 3.6V. The value measured at V_{CC} = 2.5/2.0V ± 0.2 is under the value of V_{CC} = 3.6V
- I_{CC2} = 40 mA with 70 ns cycle at V_{CC} = 2.7 ~ 3.6V, but the value is not 100% tested but obtained statistically
I_{CC2} = 25 mA with 120 ns cycle at V_{CC} = 2.5V ± 0.2, but the value is not 100% tested but obtained statistically
I_{CC2} = 15 mA with 300 ns cycle at V_{CC} = 1.8~ 2.3V, but the value is not 100% tested but obtained statistically
- The value is not 100% tested but obtained statistically at Temp = 25°C
- The value has a difference by ± 1 μA.
- I_{SB1} = 10μA for V_{CC} = 2.3 ~ 3.6V
I_{SB1} = 6μA for V_{CC} = 1.8 ~ 2.3V

GLT6200L08/M08/N08**AC Timing Characteristics**

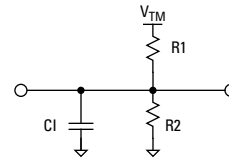
Symbol	Parameter	-70		-85		-100		-120		-150		-300		Unit	
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max		
t _{RC}	Read	Read Cycle Time	70	-	85	-	100	-	120	-	150	-	300	-	ns
t _{AA}		Address Access Time	-	70	-	85	-	100	-	120	-	150	-	300	ns
t _{CO}		Chip Select to Output	-	70	-	85	-	100	-	120	-	150	-	300	ns
t _{OE}		Output Enable to Valid Output	-	35	-	45	-	50	-	60	-	75	-	150	ns
t _{LZ}		Chip Select To Low-Z Output	10	-	10	-	10	-	10	-	20	-	50	-	ns
t _{OLZ}		Output enable to Low-Z Output	5	-	5	-	5	-	5	-	10	-	30	-	ns
t _{HZ}		Chip Disable To High-Z Output	0	25	0	25	0	30	0	35	0	40	0	60	ns
t _{OHZ}		Output Disable to High-Z Output	0	25	0	25	0	30	0	35	0	40	0	60	ns
t _{OH}		Output Hold From Address Change	10	-	15	-	15	-	15	-	15	-	30	-	ns
t _{WC}	Write	Write Cycle Time	70	-	85	-	100	-	120	-	150	-	300	-	ns
t _{CW}		Chip Select to end of Write	65	-	70	-	80	-	100	-	120	-	300	-	ns
t _{AS}		Address Set-up time	0	-	0	-	0	-	0	-	0	-	0	-	ns
t _{AW}		Address Valid to end of Write	65	-	70	-	80	-	100	-	120	-	300	-	ns
t _{WP}		Write Pulse Width	55	-	60	-	70	-	80	-	100	-	200	-	ns
t _{WR}		Write Recovery time	0	-	0	-	0	-	0	-	0	-	0	-	ns
t _{WHZ}		Write To Output High-Z	0	25	0	25	0	30	0	35	0	40	0	60	ns
t _{DW}		Data to Write Time Overlap	30	-	35	-	40	-	50	-	60	-	120	-	ns
t _{DH}		Data Hold From Write Time	0	-	0	-	0	-	0	-	0	-	0	-	ns
t _{OW}		End Write To Output Low-Z	5	-	5	-	5	-	5	-	5	-	20	-	ns

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Test Load and Input/Output Reference [1]

Item	Value	Remark
Input Pulse Level	0.4 V to 2.2 V	V _{CC} = 3.3 V, 3.0 V, 2.5 V
	0.4 V to 1.8 V	V _{CC} = 2.0 V
Input Rise Fall Time	5 ns	-
Input And Output Reference Voltage	1.5 V	V _{CC} = 3.3 V, 3.0 V
	1.1 V	V _{CC} = 2.5 V
	0.9 V	V _{CC} = 2.0 V
Output Load	C _L = 100 PF + 1TTL	See Test Condition #2
	C _L = 30 PF + 1TTL	

1. See test condition of DC and Operating Characteristics



NOTE:
 1. Including Scope and jig capacitance
 2. R1 = 3070Ω, R2 = 3150Ω
 3. V_{TM} = 2.8 for V_{CC} = 3.0/3.3V, 2.3V for V_{CC} = 2.5V, 1.8 V for V_{CC} = 2.0V

Figure 2.

Temperature and V_{CC} Conditions

Product Family	Temperature	V _{CC} Range	Typical Supply VCC	Speed (ns)
GLT6200N	Commercial 0 °C to +70°C	1.8 (min) ~ 2.3V (max)	2.0 ± 0.2V	150 ^[1] / 300
GLT6200M		2.3 (min) ~ 2.7V (max)	2.5 ± 0.2V	100 ^[1] / 120 / 150
GLT6200L		2.7 (min) ~ 3.6V (max)	3.0 ± 0.3V	85 ^[1] / 100
GLT6200L		3.0 (min) ~ 3.6V (max)	3.3 ± 0.3V	70 ^[1] / 85
GLT6200NI	Industrial -40 °C to +85°C	1.8 (min) ~ 2.3V (max)	2.0 ± 0.2V	150 ^[1] / 300
GLT6200MI		2.3 (min) ~ 2.7V (max)	2.5 ± 0.2V	100 ^[1] / 120 / 150
GLT6200LI		2.7 (min) ~ 3.6V (max)	3.0 ± 0.3V	85 ^[1] / 100
GLT6200LI		3.0 (min) ~ 3.6V (max)	3.3 ± 0.3V	70 ^[1] / 85

1. Parameters are measured with 30 pF test load

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Data Retention Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Units	
V_{DR}	V_{CC} For Data Retention	$\overline{CS1} \geq V_{CC} - 0.2 V$, $CS2 \geq V_{CC} - 0.2 V$ or $CS2 \leq 0.2 V$	1.5	-	3.6	V	
I_{DR}	Data Retention Current	$V_{CC} = 3.0 V$ $\overline{CS1} \geq V_{CC} - 0.2 V$, $CS2 \geq V_{CC} - 0.2 V$ or $CS2 \leq 0.2 V$	Super Low Power	-	-	2 ^[1]	μA
			Low Low Power	-	-	10 ^[1]	
t_{SDR}	Data Retention Set-up Time	See Data Retention Waveform	0	-	-	ns	
t_{RDR}	Recovery Time		t_{RC}	-	-		

- $I_{DR} = 5\mu A$ for low low power at $V_{CC} = 1.5V$
 $I_{DR} = 1\mu A$ for super low power at $V_{CC} = 1.5V$ and need special handling.

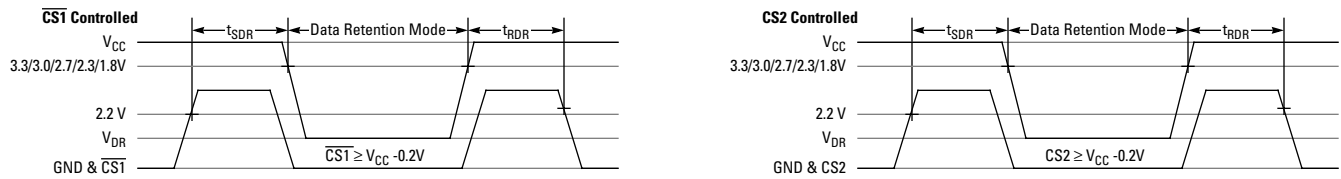
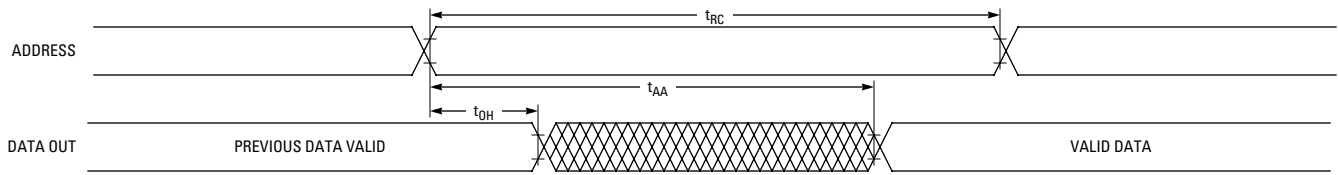


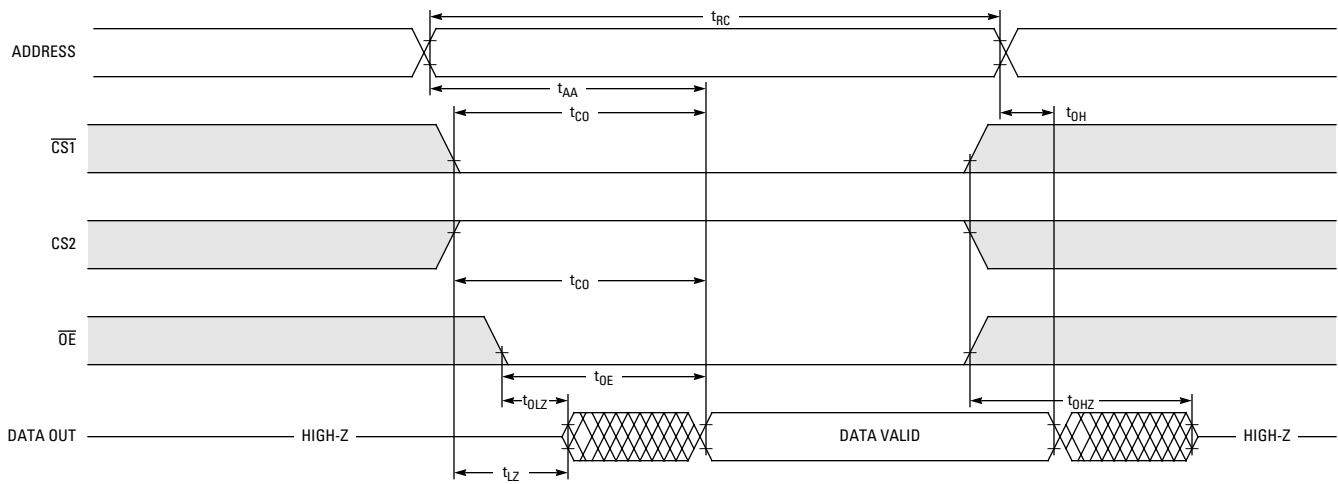
Figure 3. Data Retention Timing Diagram

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NOTE:
 1. t_{HZ} and t_{OHZ} are defined as the time at which the output achieves the open circuit conditions and are not referenced to output voltage levels.
 2. At any given temperature and voltage condition, t_{HZ} (Max) is less than t_{LZ} (Min) both for a given device and device to device interconnection.

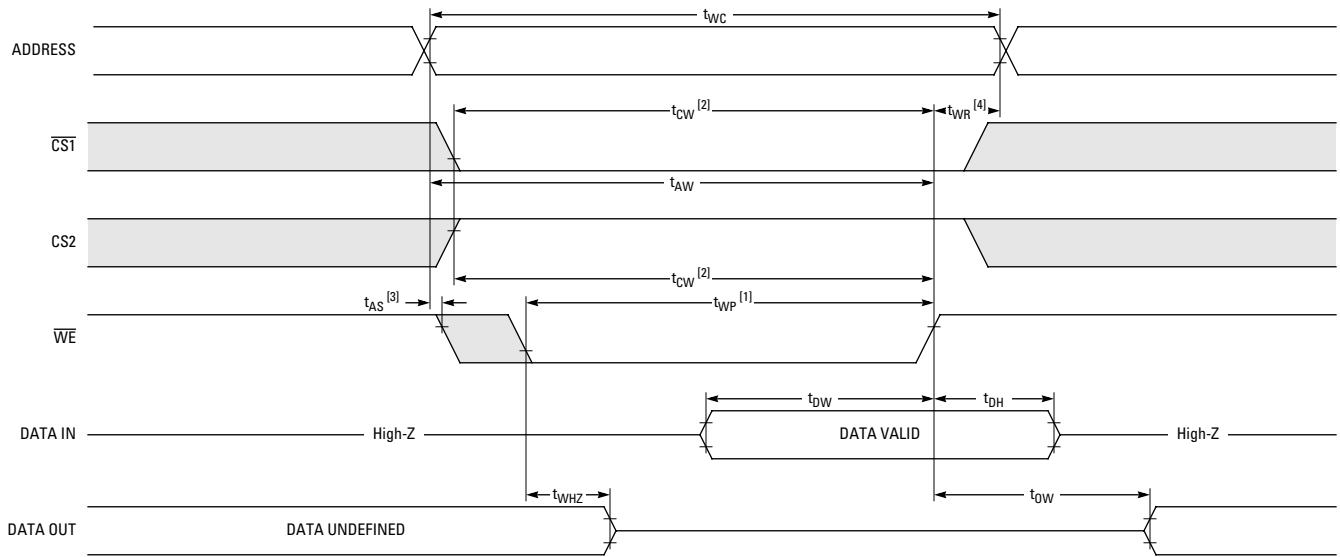
Figure 4. Read Cycle Timing (Address Controlled, $\overline{CS1} = \overline{OE} = V_{IL}$, $\overline{WE} = CS2 = V_{IH}$)



NOTE:
 1. t_{HZ} and t_{OHZ} are defined as the time at which the output achieves the open circuit conditions and are not referenced to output voltage levels.
 2. At any given temperature and voltage condition, t_{HZ} (Max) is less than t_{LZ} (Min) both for a given device and device to device interconnection.

Figure 5. Read Cycle Timing ($\overline{WE} = V_{IH}$)

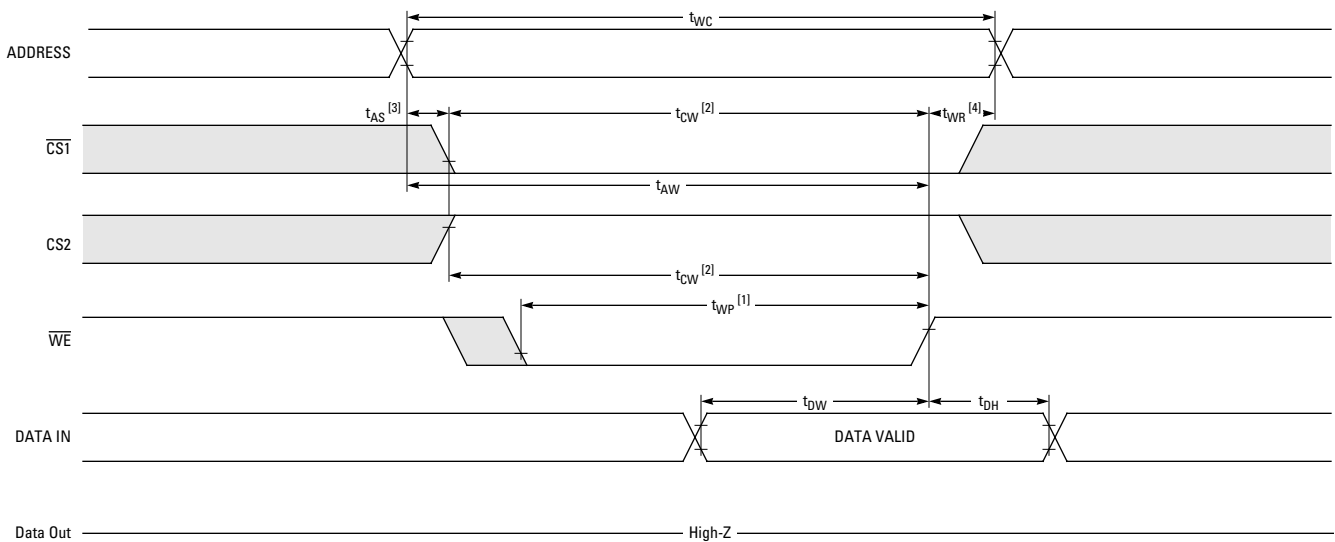
GLT6200L08/M08/N08



NOTE:

1. A write occurs during the overlap of a low $\overline{CS1}$, A high $\overline{CS2}$ and a low \overline{WE} . A write begins at the latest transition among $\overline{CS1}$ going low and \overline{WE} going low. A write ends at the earliest transition among $\overline{CS1}$ goes high and \overline{WE} going high, $t_{WP}^{[1]}$ is measured from the beginning of write to the end of write.
2. $t_{CW}^{[2]}$ is measured from the later of $\overline{CS1}$ going low to the end of write.
3. $t_{AS}^{[3]}$ is measured from the address valid to the beginning of write.
4. $t_{WR}^{[4]}$ is measured from the end of write to the address change. $t_{WR1}^{[4]}$ applied encase a write ends at $\overline{CS1}$, or \overline{WE} going high.

Figure 6. Write Cycle Timing (\overline{WE} Controlled)

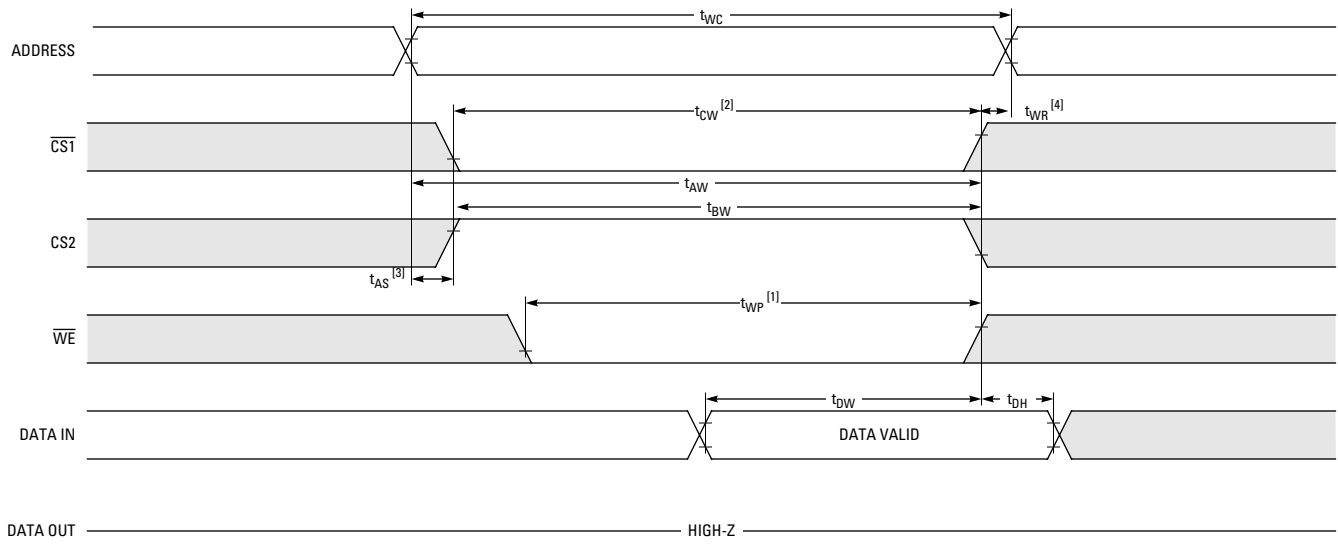


NOTE:

1. A write occurs during the overlap of a low $\overline{CS1}$, A high $\overline{CS2}$ and a low \overline{WE} . A write begins at the latest transition among $\overline{CS1}$ going low and \overline{WE} going low. A write ends at the earliest transition among $\overline{CS1}$ goes high and \overline{WE} going high, $t_{WP}^{[1]}$ is measured from the beginning of write to the end of write.
2. $t_{CW}^{[2]}$ is measured from the later of $\overline{CS1}$ going low to the end of write.
3. $t_{AS}^{[3]}$ is measured from the address valid to the beginning of write.
4. $t_{WR}^{[4]}$ is measured from the end of write to the address change. $t_{WR1}^{[4]}$ applied encase a write ends at $\overline{CS1}$, or \overline{WE} going high.

Figure 7. Write Cycle Timing ($\overline{CS1}$ Controlled)

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NOTE:

1. A write occurs during the overlap of a low $\overline{CS1}$, A high $\overline{CS2}$ and a low \overline{WE} . A write begins at the latest transition among $\overline{CS1}$ going and \overline{WE} going low. A write ends at the earliest transition among $\overline{CS1}$ goes high and \overline{WE} going high, $t_{WP}^{[1]}$ is measured from the beginning of write to the end of write.
2. $t_{CW}^{[2]}$ is measured from the later of $\overline{CS1}$ going low to the end of write.
3. $t_{AS}^{[3]}$ is measured from the address valid to the beginning of write.
4. $t_{WR}^{[4]}$ is measured from the end of write to the address change. $t_{WR1}^{[4]}$ applied encase a write ends at $\overline{CS1}$, or \overline{WE} going high.

Figure 8. Write Cycle Timing (CS2 Controlled)

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PACKAGING INFORMATION

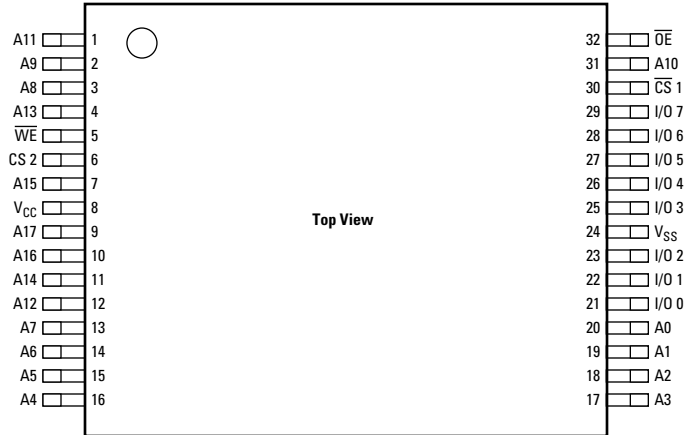
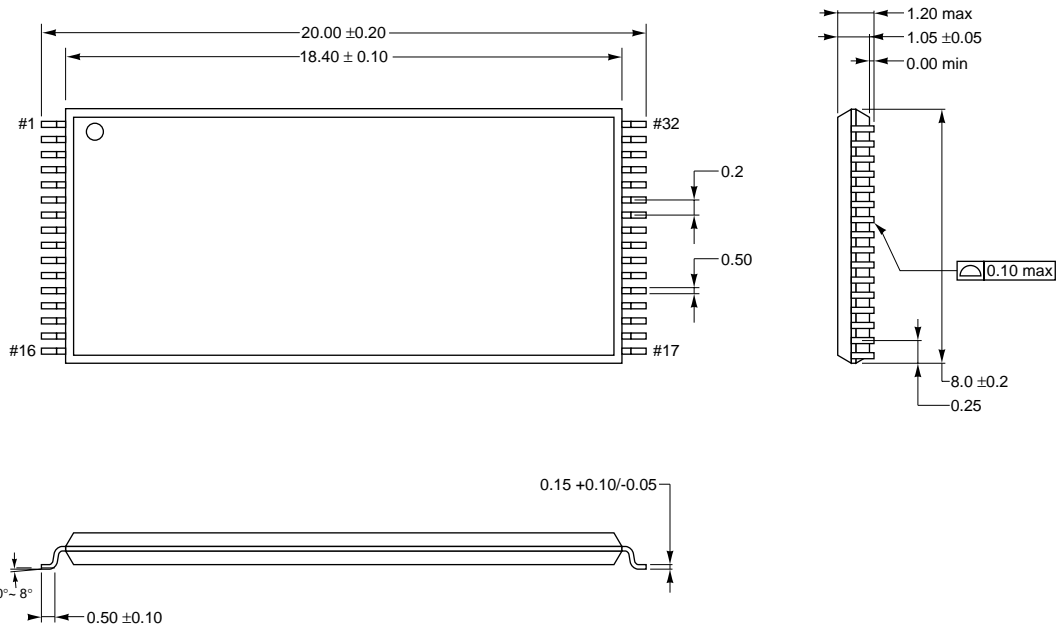
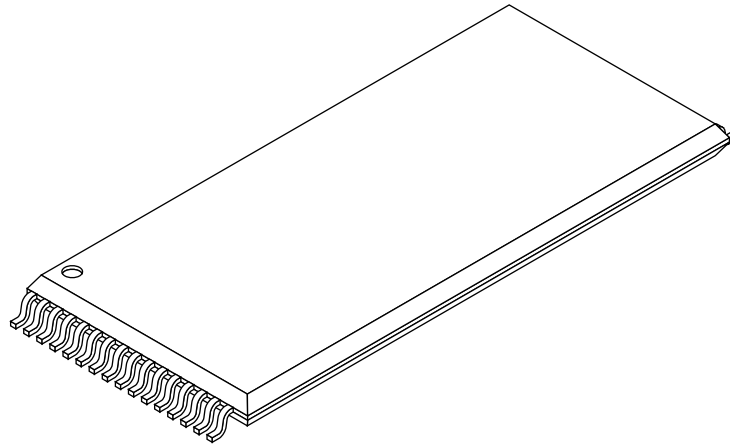


Figure 9. 32-Pin TSOP and sTSOP I Pin Assignment

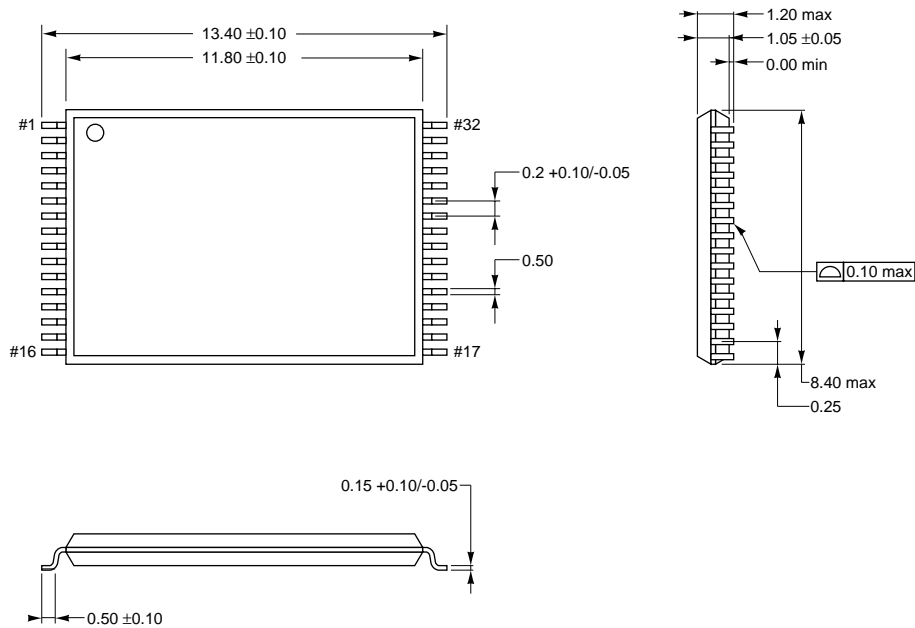
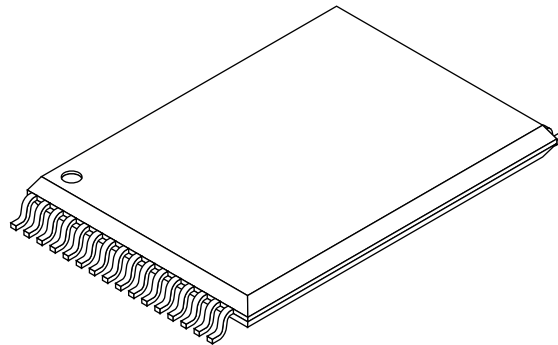
GLT6200L08/M08/N08



Dimensions in millimeters

Figure 10. 32-Pin TSOP (Type I) 8 x20 Forward Package Dimensions

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Dimensions in millimeters

Figure 11. 32-Pin sTSSOP (Type I) 8 x13.4 Forward Package Dimensions

GLT6200L08/M08/N08**ORDERING INFO****GLT6200x08LL**

Part Number	Standby Current	Cycle Time	V _{CC} Range	Temperature	Orientation	Package
GLT6200L08LL-70TS	10 μ A	70 ns	3.0 ~ 3.6	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200L08LL-85TS	10 μ A	85 ns	2.7 ~ 3.6	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200L08LL-70ST	10 μ A	70 ns	3.0 ~ 3.6	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200L08LL-85ST	10 μ A	85 ns	2.7 ~ 3.6	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200M08LL-100TS	10 μ A	100 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LL-120TS	10 μ A	120 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LL-100ST	10 μ A	100 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LL-120ST	10 μ A	120 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LL-150TS	10 μ A	150 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LL-150ST	10 μ A	150 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LL-300TS	10 μ A	300 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200N08LL-300ST	10 μ A	300 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)

GLT6200x08LLI

Part Number	Standby Current	Cycle Time	V _{CC} Range	Temperature	Orientation	Package
GLT6200L080LLI-70TS	10 μ A	70 ns	3.0 ~ 3.6	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200L080LLI-85TS	10 μ A	85 ns	2.7 ~ 3.6	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200L080LLI-70ST	10 μ A	70 ns	3.0 ~ 3.6	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200L080LLI-85ST	10 μ A	85 ns	2.7 ~ 3.6	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200M08LLI-100TS	10 μ A	100 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LLI-120TS	10 μ A	120 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LLI-100ST	10 μ A	100 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08LLI-120ST	10 μ A	120 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LLI-150TS	10 μ A	150 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LLI-150ST	10 μ A	150 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08LLI-300TS	10 μ A	300 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200N08LLI-300ST	10 μ A	300 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)

GLT6200L08/M08/N08**GLT6200x08SL**

Part Number	Standby Current	Cycle Time	V _{CC} Range	Temperature	Orientation	Package
GLT6200L08SL-70TS	2 μ A	70 ns	3.0 ~ 3.6	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200L08SL-85TS	2 μ A	85 ns	3.0 ~ 3.6	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200L08SL-70ST	2 μ A	70 ns	2.7 ~ 3.6	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200L08SL-85ST	2 μ A	85 ns	2.7 ~ 3.6	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200M08SL-100TS	2 μ A	100 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SL-120TS	2 μ A	120 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SL-100ST	2 μ A	100 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SL-120ST	2 μ A	120 ns	2.3 ~ 2.7	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SL-150TS	2 μ A	150 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SL-150ST	2 μ A	150 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SL-300TS	2 μ A	300 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin TSOP I (330mil)
GLT6200N08SL-300ST	2 μ A	300 ns	1.8 ~ 2.3	Commercial	Forward	32-Pin s-TSOP I (330mil)

GLT6200x08SLI

Part Number	Standby Current	Cycle Time	V _{CC} Range	Temperature	Orientation	Package
GLT6200L080SLI-70TS	2 μ A	70 ns	3.0 ~ 3.6	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200L080SLI-85TS	2 μ A	85 ns	3.0 ~ 3.6	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200L080SLI-70ST	2 μ A	70 ns	2.7 ~ 3.6	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200L080SLI-85ST	2 μ A	85 ns	2.7 ~ 3.6	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200M08SLI-100TS	2 μ A	100 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SLI-120TS	2 μ A	120 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SLI-100ST	2 μ A	100 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200M08SLI-120ST	2 μ A	120 ns	2.3 ~ 2.7	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SLI-150TS	2 μ A	150 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SLI-150ST	2 μ A	150 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)
GLT6200N08SLI-300TS	2 μ A	300 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin TSOP I (330mil)
GLT6200N08SLI-300ST	2 μ A	300 ns	1.8 ~ 2.3	Industrial	Forward	32-Pin s-TSOP I (330mil)



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